



LPV7215 マイクロパワー、CMOS入力、RRIO、1.8V、プッシュプル出力 コンパレータ

1 特長

- ($V^+ = 1.8V$ について、特に記載のない限り標準値)
- 非常に低い消費電力: 580nA
- 広い電源電圧範囲: 1.8V~5.5V
- 伝搬遅延: 4.5 μ s
- プッシュプル出力電流駆動: 19mA (5V時)
- 温度範囲: -40°C~125°C
- レール・ツー・レール入力
- 小型の5ピンSOT-23およびSC70パッケージ

2 アプリケーション

- RCタイマ
- ウィンドウ検出器
- IR受信機
- マルチバイブレータ
- アラームおよび監視回路

3 概要

LPV7215デバイスは超低消費電力のコンパレータで、消費電流の標準値は580nAです。TIの低消費電力コンパレータの中でも、クラス最高の消費電流と伝搬遅延性能を実現しています。1.8Vの電源と100mVのオーバードライブで、伝搬遅延はわずか4.5 μ sです。

1.8V~5.5Vの広い電源電圧範囲で動作するように設計されており、1.8V、2.7V、5Vでの動作が規定されているため、LPV7215は各種のバッテリー駆動アプリケーションに最適です。LPV7215は、レール・ツー・レールのコモンモード電圧範囲を持つため、単一電源での動作に適しています。

プッシュプル出力段を備えたLPV7215は、いかなる容量性負荷あるいは抵抗性負荷を駆動した場合にも、絶対最小消費電力で動作させることができます。

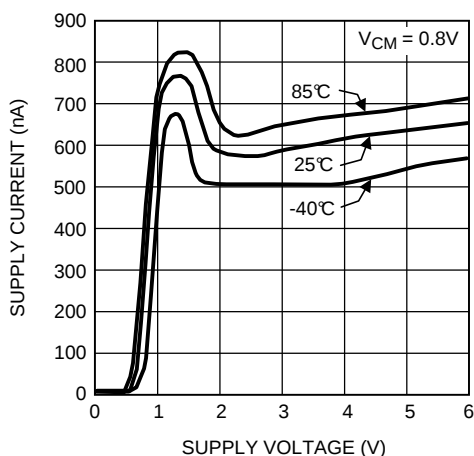
いくつかの省スペース・パッケージを選択できるため、ハンドヘルド電子機器や携帯電話アプリケーションでの使用に最適です。LPV7215は、TIの先進のVIP50プロセスで製造されます。

製品情報⁽¹⁾

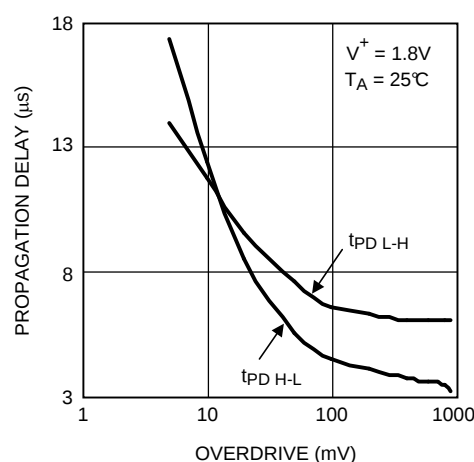
型番	パッケージ	本体サイズ (公称)
LPV7215	SOT-23 (5)	2.90mm×1.60mm
	SC70 (5)	2.00mm×1.25mm

(1) 利用可能なすべてのパッケージについては、このデータシートの末尾にある注文情報を参照してください。

消費電流と電源電圧との関係



伝搬遅延とオーバードライブとの関係



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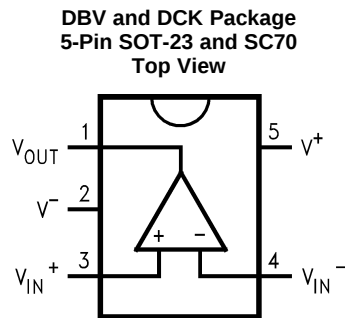
4 改訂履歴

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

Revision I (April 2013) から Revision J に変更	Page
「ESD 定格」表、「機能説明」セクション、「デバイスの機能モード」セクション、「アプリケーションと実装」セクション、「電源に関する推奨事項」セクション、「レイアウト」セクション、「デバイスおよびドキュメントのサポート」セクション、「メカニカル、パッケージ、および注文情報」セクション 追加 - Updated values in the <i>Thermal Information</i> table to align with JEDEC standards.	 1 4

Revision H (April 2013) から Revision I に変更	Page
Changed layout of National Data Sheet to TI format	22

5 Pin Configuration and Functions



Pin Functions

PIN		I/O	DESCRIPTION
NO.	NAME		
1	V _{OUT}	O	Output
2	V ⁻	P	Negative Supply
3	V _{IN} ⁺	I	Noninverting Input
4	V _{IN} ⁻	I	Inverting Input
5	V ⁺	P	Positive Supply

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

	MIN	MAX	UNIT
V _{IN} differential	-2.5	2.5	V
Supply voltage (V ⁺ - V ⁻)		6	V
Voltage at input and output pins	V ⁻ - 0.3	V ⁺ + 0.3	V
Junction temperature, T _J ⁽²⁾		150	°C
Storage temperature, T _{stg}	-65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) The maximum power dissipation is a function of T_{J(MAX)}, θ_{JA}. The maximum allowable power dissipation at any ambient temperature is P_D = (T_{J(MAX)} - T_A) / θ_{JA}. All numbers apply for packages soldered directly onto a PCB.

6.2 ESD Ratings

		VALUE	UNIT
V _(ESD) Electrostatic discharge	Human-body model (HBM) ⁽¹⁾	±2000	V
	Machine model (MM) ⁽²⁾	±200	

- (1) Human-body model, applicable std. MIL-STD-883, Method 3015.7.
- (2) Machine model, applicable std. JESD22-A115-A (ESD MM std. of JEDEC) Field-Induced Charge-Device Model, applicable std. JESD22-C101-C (ESD FICDM std. of JEDEC).

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

	MIN	MAX	UNIT
Temperature ⁽¹⁾	–40	125	°C
Supply voltage ($V^+ - V^-$)	1.8	5.5	V

- (1) The maximum power dissipation is a function of $T_{J(MAX)}$, θ_{JA} . The maximum allowable power dissipation at any ambient temperature is $P_D = (T_{J(MAX)} - T_A) / \theta_{JA}$. All numbers apply for packages soldered directly onto a PCB.

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾		LPV7215		UNIT
		DBV (SOT-23)	DCK (SC70)	
		5 PINS	5 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance ⁽²⁾	234	456	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	153	110.8	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	51.7	59.8	°C/W
ψ_{JT}	Junction-to-top characterization parameter	38	3.6	°C/W
ψ_{JB}	Junction-to-board characterization parameter	51.2	59	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	n/a	n/a	°C/W

- (1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.
- (2) The maximum power dissipation is a function of $T_{J(MAX)}$, θ_{JA} . The maximum allowable power dissipation at any ambient temperature is $P_D = (T_{J(MAX)} - T_A) / \theta_{JA}$. All numbers apply for packages soldered directly onto a PCB.

6.5 Electrical Characteristics: 1.8 V

 Unless otherwise specified, all limits are specified for $T_A = 25^\circ\text{C}$, $V^+ = 1.8\text{V}$, $V^- = 0\text{V}$, and $V_{CM} = V^+/2$, $V_O = V^-$.⁽¹⁾

PARAMETER		TEST CONDITIONS	MIN ⁽²⁾	TYP ⁽³⁾	MAX ⁽²⁾	UNIT
I_S	Supply current	$V_{CM} = 0.3\text{V}$	$T_A = 25^\circ\text{C}$	580	750	nA
			Temperature extremes		1050	
	$V_{CM} = 1.5\text{V}$	$T_A = 25^\circ\text{C}$		790	980	
			Temperature extremes		1300	
V_{OS}	Input offset voltage	$V_{CM} = 0\text{V}$	$T_A = 25^\circ\text{C}$	± 0.3	± 6	mV
			Temperature extremes		± 8	
	$V_{CM} = 1.8\text{V}$	$T_A = 25^\circ\text{C}$		± 0.4	± 5	
			Temperature extremes		± 7	
TCV_{OS}	Input offset average drift	See ⁽⁴⁾		± 1		$\mu\text{V}/^\circ\text{C}$
I_B	Input bias current ⁽⁵⁾	$V_{CM} = 1.6\text{V}$		–40		fA
I_{OS}	Input offset current			10		fA

- (1) Electrical table values apply only for factory testing conditions at the temperature indicated. Factory testing conditions result in very limited self-heating of the device.
- (2) Limits are 100% production tested at 25°C . Limits over the operating temperature range are specified through correlations using statistical quality control (SQC) method.
- (3) Typical values represent the most likely parametric norm as determined at the time of characterization. Actual typical values may vary over time and also depend on the application and configuration. The typical values are not tested and are not specified on shipped production material.
- (4) Offset voltage average drift determined by dividing the change in V_{OS} at temperature extremes into the total temperature change.
- (5) Positive current corresponds to current flowing into the device.

Electrical Characteristics: 1.8 V (continued)

Unless otherwise specified, all limits are specified for $T_A = 25^\circ\text{C}$, $V^+ = 1.8\text{V}$, $V^- = 0\text{V}$, and $V_{CM} = V^+/2$, $V_O = V^-$.⁽¹⁾

PARAMETER		TEST CONDITIONS		MIN ⁽²⁾	TYP ⁽³⁾	MAX ⁽²⁾	UNIT
CMRR	Common-mode rejection ratio	V_{CM} Stepped from 0 V to 0.7 V	$T_A = 25^\circ\text{C}$	66	88		dB
			Temperature extremes	62			
		V_{CM} Stepped from 1.2 V to 1.8 V	$T_A = 25^\circ\text{C}$	68	87		
			Temperature extremes	62			
		V_{CM} Stepped from 0 V to 1.8 V	$T_A = 25^\circ\text{C}$	44	77		
			Temperature extremes	43			
PSRR	Power supply rejection ratio	$V^+ = 1.8\text{V}$ to 5.5 V, $V_{CM} = 0\text{V}$	$T_A = 25^\circ\text{C}$	66	82		dB
			Temperature extremes	63			
CMVR	Input common-mode voltage range	CMRR $\geq 40\text{ dB}$	Temperature Extremes	-0.1		1.9	V
A_V	Voltage gain				120		dB
V_O	Output swing high	$I_O = 500\text{ }\mu\text{A}$	$T_A = 25^\circ\text{C}$	1.63	1.69		V
			Temperature extremes	1.58			
		$I_O = 1\text{ mA}$	$T_A = 25^\circ\text{C}$	1.46	1.6		
			Temperature extremes	1.37			
	Output swing low	$I_O = -500\text{ }\mu\text{A}$	$T_A = 25^\circ\text{C}$		88	180	mV
			Temperature extremes			230	
		$I_O = -1\text{ mA}$	$T_A = 25^\circ\text{C}$		180	310	
			Temperature extremes			400	
I_{OUT}	Output current	Source $V_O = V^+/2$	$T_A = 25^\circ\text{C}$	1.75	2.26		mA
			Temperature extremes	1.3			
		Sink $V_O = V^+/2$	$T_A = 25^\circ\text{C}$	2.35	3.1		
			Temperature extremes	1.45			
	Propagation delay (high to low)	Overdrive = 10 mV			13		μs
		Overdrive = 100 mV	$T_A = 25^\circ\text{C}$		4.5	6.5	
			Temperature extremes			9	
	Propagation delay (low to high)	Overdrive = 10 mV			12.5		μs
		Overdrive = 100 mV	$T_A = 25^\circ\text{C}$		6.6	9	
			Temperature extremes			12	
t_{rise}	Rise time	Overdrive = 10 mV $C_L = 30\text{ pF}$, $R_L = 1\text{ M}\Omega$			80		ns
		Overdrive = 100 mV $C_L = 30\text{ pF}$, $R_L = 1\text{ M}\Omega$			75		
t_{fall}	Fall time	Overdrive = 10 mV $C_L = 30\text{ pF}$, $R_L = 1\text{ M}\Omega$			70		ns
		Overdrive = 100 mV $C_L = 30\text{ pF}$, $R_L = 1\text{ M}\Omega$			65		

6.6 Electrical Characteristics: 2.7 V

Unless otherwise specified, all limits are specified for $T_A = 25^\circ\text{C}$, $V^+ = 2.7\text{ V}$, $V^- = 0\text{ V}$, and $V_{CM} = V^+/2$, $V_O = V^-$.⁽¹⁾

PARAMETER		TEST CONDITIONS		MIN ⁽²⁾	TYP ⁽³⁾	MAX ⁽²⁾	UNIT
I_S	Supply current	$V_{CM} = 0.3\text{ V}$	$T_A = 25^\circ\text{C}$		605	780	nA
			Temperature extremes			1100	
		$V_{CM} = 2.4\text{ V}$	$T_A = 25^\circ\text{C}$		815	1010	
			Temperature extremes			1350	
V_{OS}	Input offset voltage	$V_{CM} = 0\text{ V}$	$T_A = 25^\circ\text{C}$		± 0.3	± 6	mV
			Temperature extremes			± 8	
		$V_{CM} = 2.7\text{ V}$	$T_A = 25^\circ\text{C}$		± 0.3	± 5	
			Temperature extremes			± 7	
TCV_{OS}	Input offset average drift	See ⁽⁴⁾			± 1		$\mu\text{V/C}$
I_B	Input bias current ⁽⁵⁾	$V_{CM} = 1.8\text{ V}$			-40		fA
I_{OS}	Input offset current				20		fA
CMRR	Common-mode rejection ratio	V_{CM} Stepped from 0 V to 1.6 V	$T_A = 25^\circ\text{C}$		72	90	dB
			Temperature extremes		66		
		V_{CM} Stepped from 2.1V to 2.7V	$T_A = 25^\circ\text{C}$		71	94	
			Temperature extremes		63		
		V_{CM} Stepped from 0 V to 2.7 V	$T_A = 25^\circ\text{C}$		47	80	
			Temperature extremes		46		
PSRR	Power supply rejection ratio	$V^+ = 1.8\text{ V to } 5.5\text{ V}$, $V_{CM} = 0\text{ V}$	$T_A = 25^\circ\text{C}$		66	82	dB
			Temperature extremes		63		
CMVR	Input common-mode voltage range	CMRR $\geq 40\text{ dB}$	Temperature extremes	-0.1		2.8	V
A_V	Voltage gain				120		dB
V_O	Output swing high	$I_O = 500\text{ }\mu\text{A}$	$T_A = 25^\circ\text{C}$		2.57	2.62	V
			Temperature extremes		2.53		
		$I_O = 1\text{ mA}$	$T_A = 25^\circ\text{C}$		2.47	2.53	
			Temperature extremes		2.4		
	Output swing low	$I_O = -500\text{ }\mu\text{A}$	$T_A = 25^\circ\text{C}$		60	130	mV
			Temperature extremes			190	
		$I_O = -1\text{ mA}$	$T_A = 25^\circ\text{C}$		120	250	
			Temperature extremes			330	

(1) Electrical table values apply only for factory testing conditions at the temperature indicated. Factory testing conditions result in very limited self-heating of the device.

(2) Limits are 100% production tested at 25°C . Limits over the operating temperature range are specified through correlations using statistical quality control (SQC) method.

(3) Typical values represent the most likely parametric norm as determined at the time of characterization. Actual typical values may vary over time and also depend on the application and configuration. The typical values are not tested and are not specified on shipped production material.

(4) Offset voltage average drift determined by dividing the change in V_{OS} at temperature extremes into the total temperature change.

(5) Positive current corresponds to current flowing into the device.

Electrical Characteristics: 2.7 V (continued)

Unless otherwise specified, all limits are specified for $T_A = 25^\circ\text{C}$, $V^+ = 2.7\text{ V}$, $V^- = 0\text{ V}$, and $V_{CM} = V^+/2$, $V_O = V^-$.⁽¹⁾

PARAMETER	TEST CONDITIONS		MIN ⁽²⁾	TYP ⁽³⁾	MAX ⁽²⁾	UNIT
I_{OUT} Output current	Source $V_O = V^+/2$	$T_A = 25^\circ\text{C}$	4.5	5.7		mA
		Temperature extremes	3.4			
	Sink $V_O = V^+/2$	$T_A = 25^\circ\text{C}$	5.6	7.5		
		Temperature extremes	3.2			
Propagation delay (high to low)	Overdrive = 10 mV			14.5		μs
	Overdrive = 100 mV	$T_A = 25^\circ\text{C}$		5.8	8.5	
		Temperature extremes			10.5	
	Overdrive = 10 mV			15		
Propagation delay (low to high)	Overdrive = 100 mV	$T_A = 25^\circ\text{C}$		7.5	10	μs
		Temperature extremes			12.5	
	Overdrive = 10 mV			15		
	Overdrive = 100 mV			7.5	10	
t_{rise} Rise time	Overdrive = 10 mV $C_L = 30\text{ pF}$, $R_L = 1\text{ M}\Omega$			90		ns
	Overdrive = 100 mV $C_L = 30\text{ pF}$, $R_L = 1\text{ M}\Omega$			85		
t_{fall} Fall time	Overdrive = 10 mV $C_L = 30\text{ pF}$, $R_L = 1\text{ M}\Omega$			85		ns
	Overdrive = 100 mV $C_L = 30\text{ pF}$, $R_L = 1\text{ M}\Omega$			75		

6.7 Electrical Characteristics: 5 V

Unless otherwise specified, all limits are specified for $T_A = 25^\circ\text{C}$, $V^+ = 5\text{ V}$, $V^- = 0\text{ V}$, and $V_{CM} = V^+/2$, $V_O = V^-$.⁽¹⁾

PARAMETER	TEST CONDITIONS		MIN ⁽²⁾	TYP ⁽³⁾	MAX ⁽²⁾	UNIT
I_S Supply current	$V_{CM} = 0.3\text{ V}$	$T_A = 25^\circ\text{C}$		612	790	nA
		Temperature extremes			1150	
	$V_{CM} = 4.7\text{ V}$	$T_A = 25^\circ\text{C}$		825	1030	
		Temperature extremes			1400	
V_{OS} Input offset voltage	$V_{CM} = 0\text{ V}$	$T_A = 25^\circ\text{C}$		± 0.3	± 6	mV
		Temperature extremes			± 8	
	$V_{CM} = 5\text{ V}$	$T_A = 25^\circ\text{C}$			± 5	
		Temperature extremes			± 7	
TCV_{OS} Input offset average drift	See ⁽⁴⁾			± 1		$\mu\text{V}/^\circ\text{C}$
I_B Input bias current ⁽⁵⁾	$V_{CM} = 4.5\text{ V}$			-400		fA
I_{OS} Input offset current				20		fA

(1) Electrical table values apply only for factory testing conditions at the temperature indicated. Factory testing conditions result in very limited self-heating of the device.

(2) Limits are 100% production tested at 25°C . Limits over the operating temperature range are specified through correlations using statistical quality control (SQC) method.

(3) Typical values represent the most likely parametric norm as determined at the time of characterization. Actual typical values may vary over time and also depend on the application and configuration. The typical values are not tested and are not specified on shipped production material.

(4) Offset voltage average drift determined by dividing the change in V_{OS} at temperature extremes into the total temperature change.

(5) Positive current corresponds to current flowing into the device.

Electrical Characteristics: 5 V (continued)

Unless otherwise specified, all limits are specified for $T_A = 25^\circ\text{C}$, $V^+ = 5\text{ V}$, $V^- = 0\text{ V}$, and $V_{CM} = V^+/2$, $V_O = V^-$. ⁽¹⁾

PARAMETER		TEST CONDITIONS		MIN ⁽²⁾	TYP ⁽³⁾	MAX ⁽²⁾	UNIT
CMRR	Common-mode rejection ratio	V_{CM} Stepped from 0 V to 3.9 V	$T_A = 25^\circ\text{C}$	72	98		dB
			Temperature extremes	66			
		V_{CM} Stepped from 4.4 V to 5 V	$T_A = 25^\circ\text{C}$	73	92		
			Temperature extremes	67			
		V_{CM} Stepped from 0 V to 5 V	$T_A = 25^\circ\text{C}$	53	82		
PSRR	Power supply rejection ratio	$V^+ = 1.8\text{ V}$ to 5.5 V, $V_{CM} = 0\text{ V}$	$T_A = 25^\circ\text{C}$	66	82		dB
			Temperature extremes	63			
CMVR	Input common-mode voltage range	CMRR $\geq 40\text{ dB}$	Temperature extremes	-0.1		5.1	V
A_V	Voltage gain				120		dB
V_O	Output swing high	$I_O = 500\text{ }\mu\text{A}$	$T_A = 25^\circ\text{C}$	4.9	4.94		V
			Temperature extremes	4.86			
		$I_O = 1\text{ mA}$	$T_A = 25^\circ\text{C}$	4.82	4.89		
			Temperature extremes	4.77			
	Output swing low	$I_O = -500\text{ }\mu\text{A}$	$T_A = 25^\circ\text{C}$		43	90	mV
			Temperature extremes			130	
		$I_O = -1\text{ mA}$	$T_A = 25^\circ\text{C}$		88	170	
			Temperature extremes			230	
I_{OUT}	Output current	Source $V_O = V^+/2$	$T_A = 25^\circ\text{C}$	13	17		mA
			Temperature extremes	7.5			
		Sink $V_O = V^+/2$	$T_A = 25^\circ\text{C}$	14.5	19		
			Temperature extremes	8.5			
	Propagation delay (high to low)	Overdrive = 10 mV			18		μs
		Overdrive = 100 mV	$T_A = 25^\circ\text{C}$		7.7	13.5	
			Temperature extremes			16	
	Propagation delay (low to high)	Overdrive = 10 mV			30		μs
		Overdrive = 100 mV	$T_A = 25^\circ\text{C}$		12	15	
			Temperature extremes			20	
t_{rise}	Rise time	Overdrive = 10 mV $C_L = 30\text{ pF}$, $R_L = 1\text{ M}\Omega$			100		ns
		Overdrive = 100 mV $C_L = 30\text{ pF}$, $R_L = 1\text{ M}\Omega$			100		
t_{fall}	Fall time	Overdrive = 10 mV $C_L = 30\text{ pF}$, $R_L = 1\text{ M}\Omega$			115		ns
		Overdrive = 100 mV $C_L = 30\text{ pF}$, $R_L = 1\text{ M}\Omega$			95		

6.8 Typical Characteristics

At $T_j = 25^\circ\text{C}$ unless otherwise specified.

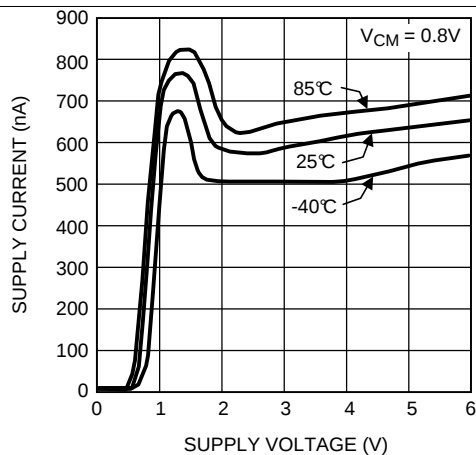


Figure 1. Supply Current vs Supply Voltage

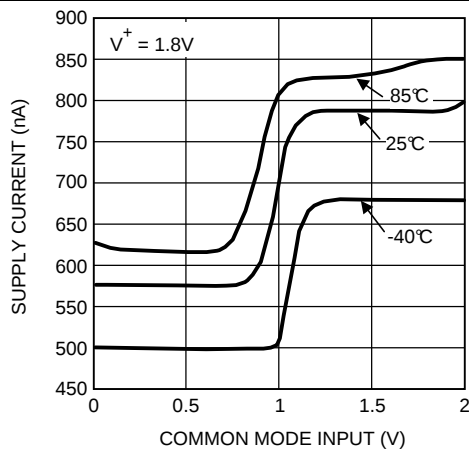


Figure 2. Supply Current vs Common-Mode Input

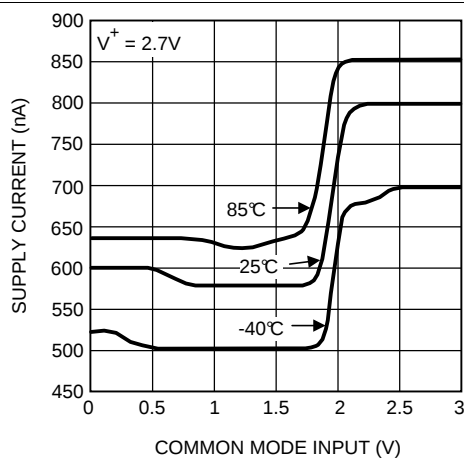


Figure 3. Supply Current vs Common-Mode Input

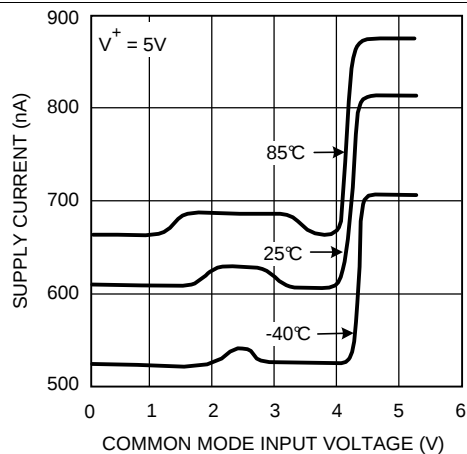


Figure 4. Supply Current vs Common-Mode Input

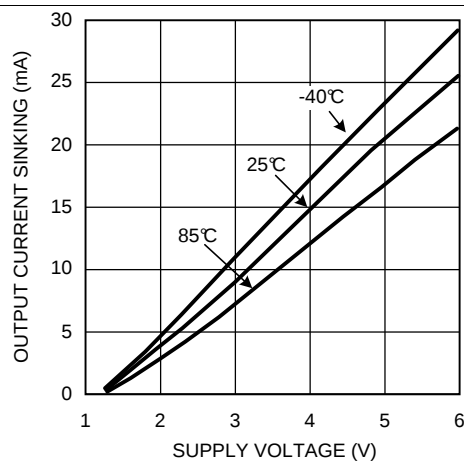


Figure 5. Short-Circuit Sinking Current vs Supply Voltage

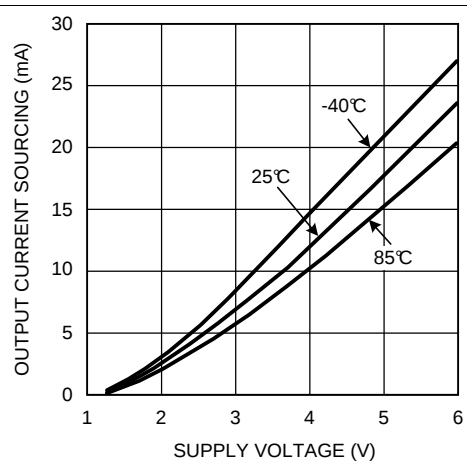


Figure 6. Short-Circuit Sourcing Current vs Supply Voltage

Typical Characteristics (continued)

At $T_J = 25^\circ\text{C}$ unless otherwise specified.

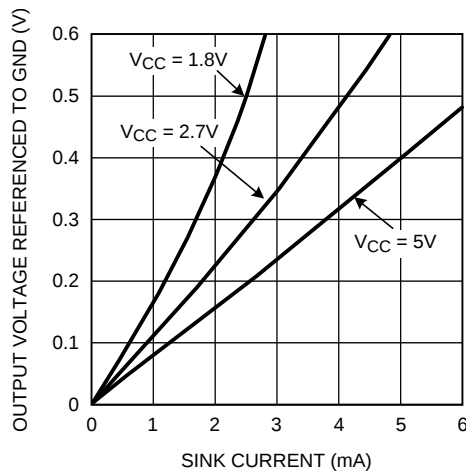


Figure 7. Output Voltage Low vs Sink Current

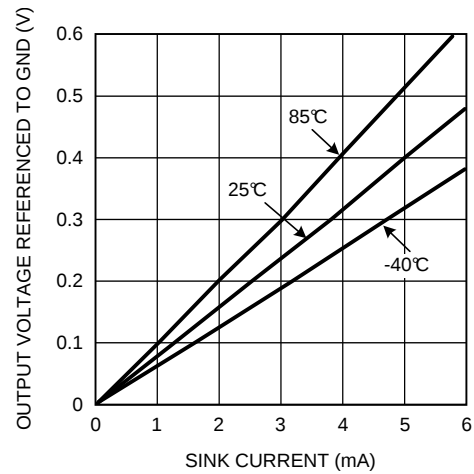


Figure 8. Output Voltage Low vs Sink Current

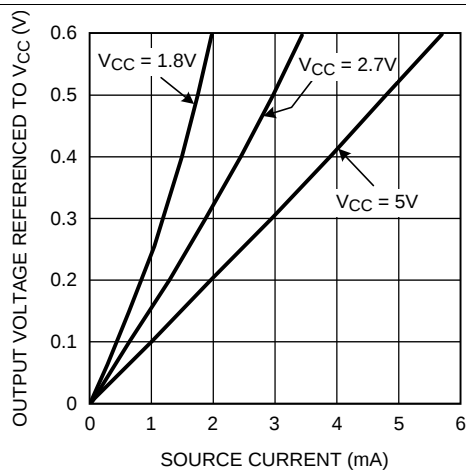


Figure 9. Output Voltage High vs Source Current

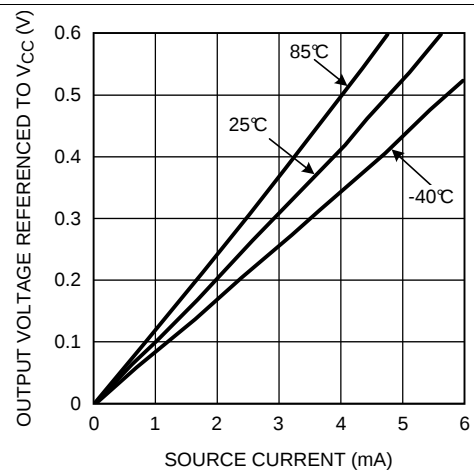


Figure 10. Output Voltage High vs Source Current

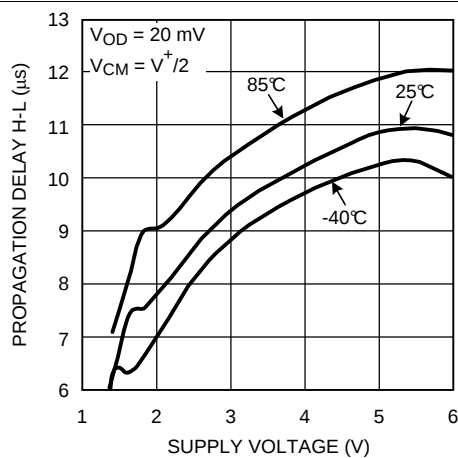


Figure 11. Propagation Delay vs Supply Voltage

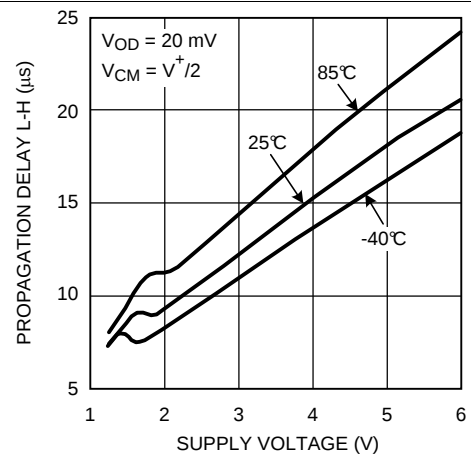


Figure 12. Propagation Delay vs Supply Voltage

Typical Characteristics (continued)

At $T_J = 25^\circ\text{C}$ unless otherwise specified.

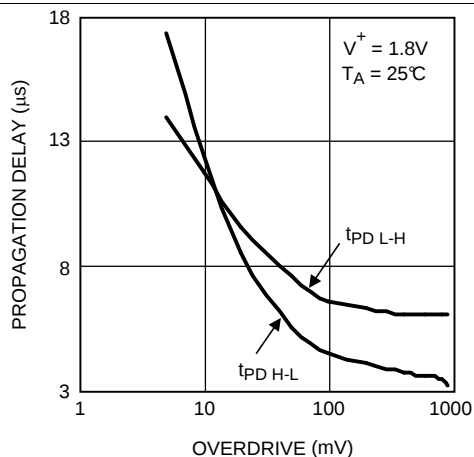


Figure 13. Propagation Delay vs Overdrive

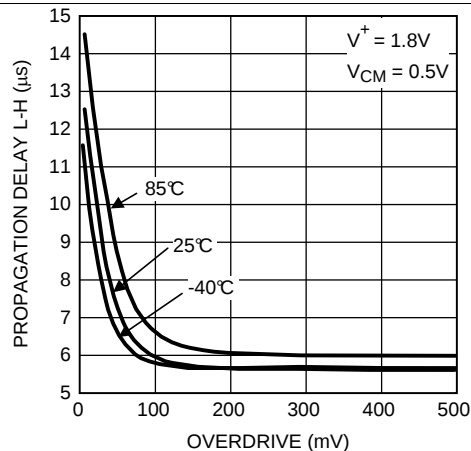


Figure 14. Propagation Delay vs Overdrive

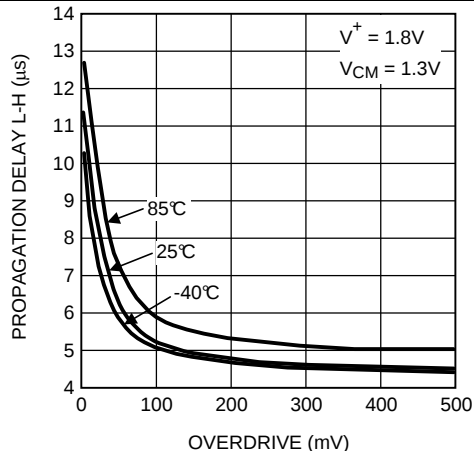


Figure 15. Propagation Delay vs Overdrive

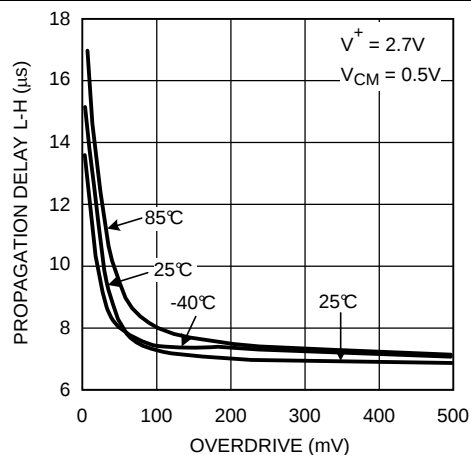


Figure 16. Propagation Delay vs Overdrive

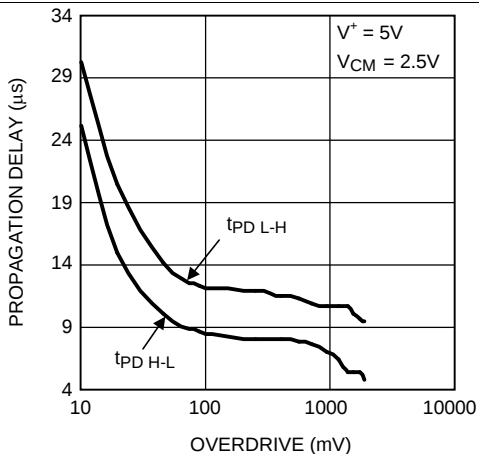


Figure 17. Propagation Delay vs Overdrive

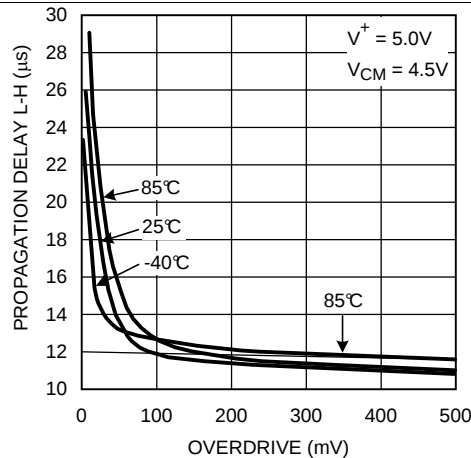


Figure 18. Propagation Delay vs Overdrive

Typical Characteristics (continued)

At $T_J = 25^\circ\text{C}$ unless otherwise specified.

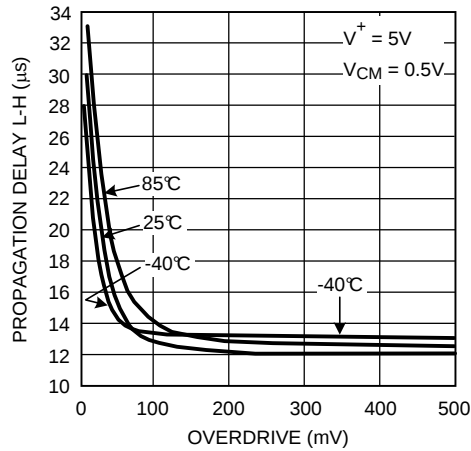


Figure 19. Propagation Delay vs Overdrive

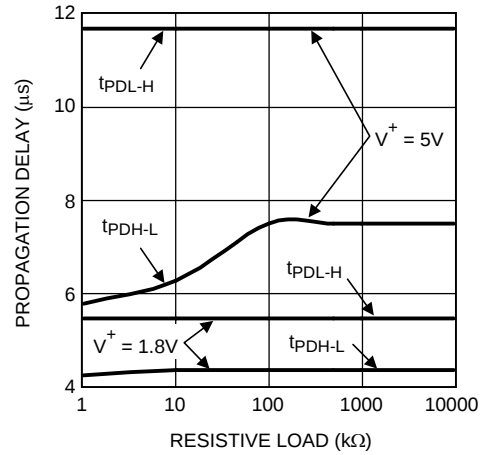


Figure 20. Propagation Delay vs Resistive Load

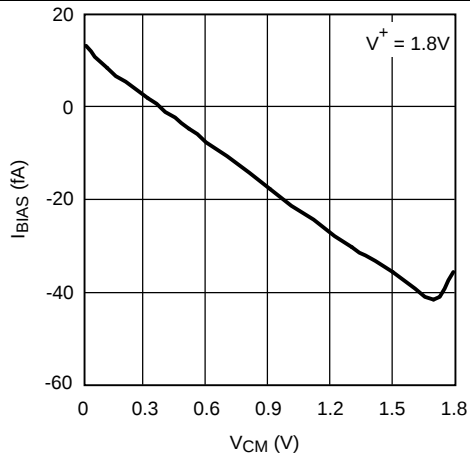


Figure 21. I_{BIAS} vs V_{CM}

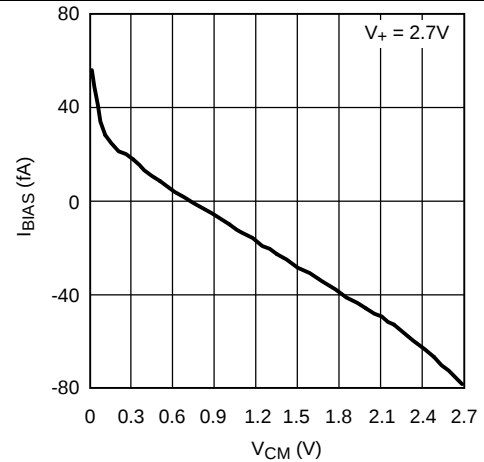


Figure 22. I_{BIAS} vs V_{CM}

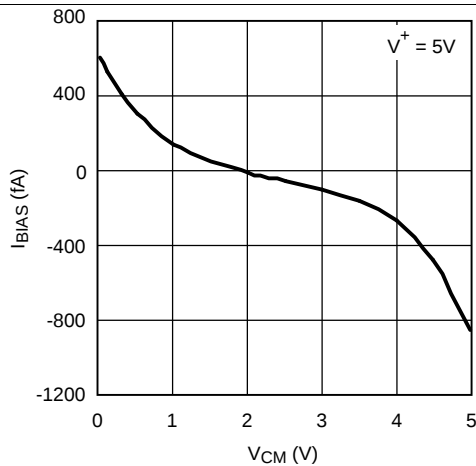


Figure 23. I_{BIAS} vs V_{CM}

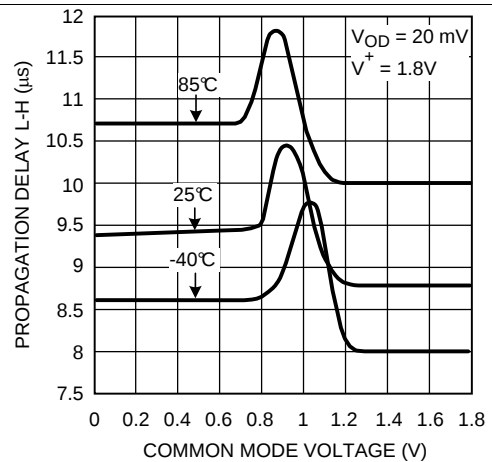


Figure 24. Propagation Delay vs Common-Mode Input

Typical Characteristics (continued)

At $T_J = 25^\circ\text{C}$ unless otherwise specified.

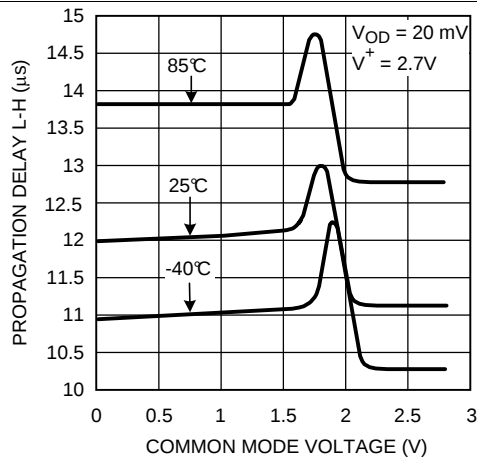


Figure 25. Propagation Delay vs Common-Mode Input

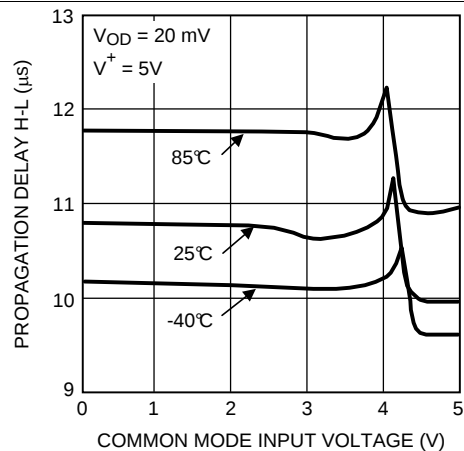


Figure 26. Propagation Delay vs Common-Mode Input

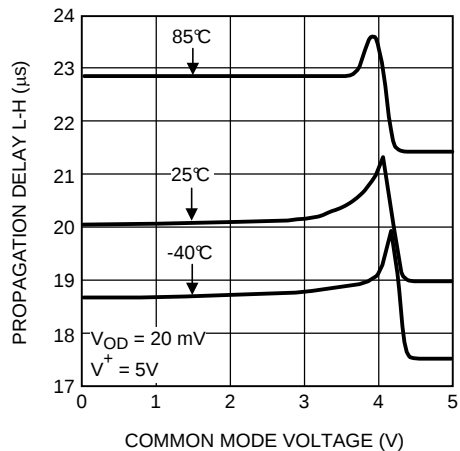


Figure 27. Propagation Delay vs Common-Mode Input

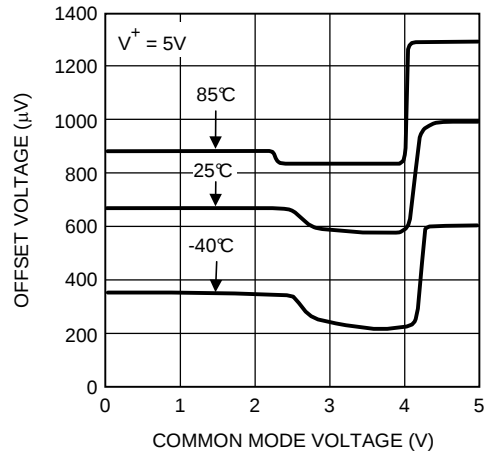


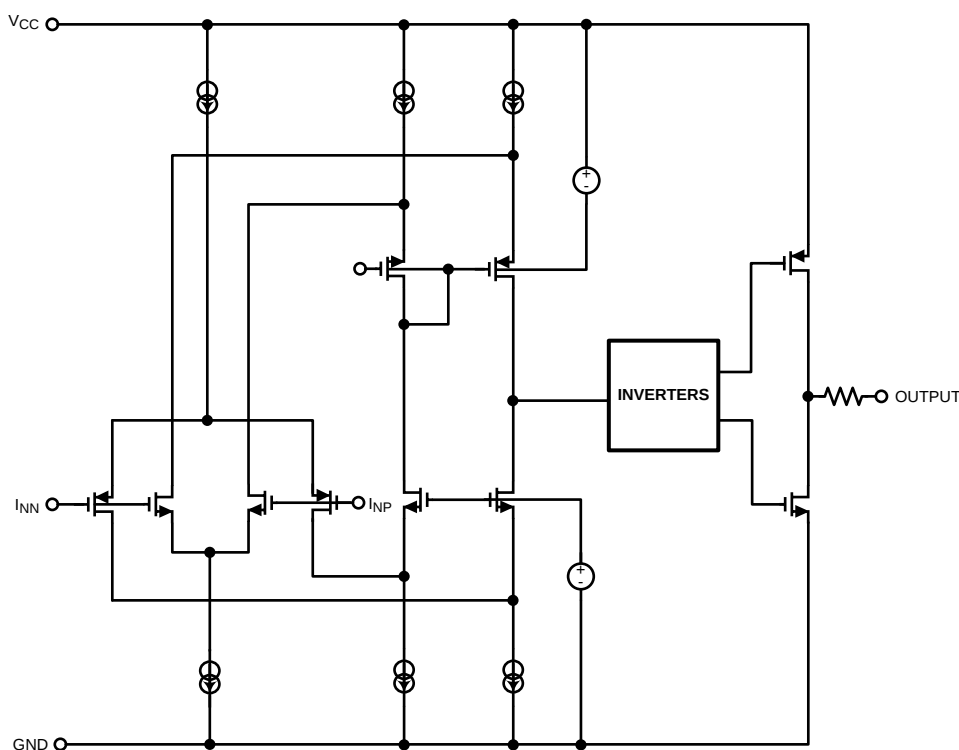
Figure 28. Offset Voltage vs Common-Mode Input

7 Detailed Description

7.1 Overview

The LPV7215 is a single-channel comparator with a push-pull output stage. This comparator is optimized for low-power consumption and single-supply operation with greater than rail-to-rail input operation. The push-pull output of the LPV7215 supports rail-to-rail output swing and interfaces with TTL/CMOS logic.

7.2 Functional Block Diagram



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7.3 Feature Description

Low supply current and fast propagation delay distinguish the LPV7215 from other low-power comparators.

7.3.1 Input Stage

The LPV7215 has rail-to-rail input common-mode voltage range. It can operate at any differential input voltage within this limit as long as the differential voltage is greater than zero. A differential input of zero volts may result in oscillation.

The differential input stage of the comparator is a pair of PMOS and NMOS transistors, therefore, no current flows into the device. The input bias current measured is the leakage current in the MOS transistors and input protection diodes. This low bias current allows the comparator to interface with a variety of circuitry and devices with minimal concern about matching the input resistances.

The input to the comparator is protected from excessive voltage by internal ESD diodes connected to both supply rails. This protects the circuit from both ESD events, as well as signals that significantly exceed the supply voltages. When this occurs the ESD protection diodes become forward-biased and draw current into these structures, resulting in no input current to the terminals of the comparator. Until this occurs, there is essentially no input current to the diodes. As a result, placing a large resistor in series with an input that may be exposed to large voltages, limits the input current but have no other noticeable effect.

Feature Description (continued)

7.3.2 Output Stage

The LPV7215 has a MOS push-pull rail-to-rail output stage. The push-pull transistor configuration of the output keeps the total system power consumption to a minimum. The only current consumed by the LPV7215 is the less than 1- μ A supply current and the current going directly into the load. No power is wasted through the pullup resistor when the output is low. The output stage is specifically designed with dead time between the time when one transistor is turned off and the other is turned on (break-before-make) to minimize shoot through currents. The internal logic controls the break-before-make timing of the output transistors. The break-before-make delay varies with temperature and power condition.

7.3.3 Output Current

Even though the LPV7215 uses less than 1- μ A supply current, the outputs are able to drive very large currents. The LPV7215 can source up to 17 mA and can sink up to 19 mA, when operated at 5-V supply. This large current handling capability allows driving heavy loads directly.

7.3.4 Response Time

Depending upon the amount of overdrive, the propagation delay is typically 6 to 30 μ s. The curves showing propagation delay vs overdrive in the [Typical Characteristics](#) section shows the delay time when the input is preset with 100 mV across the inputs and then is driven the other way by 10 mV to 500 mV.

The output signal can show a step during switching depending on the load. A fast RC time constant due to both small capacitive and resistive loads shows a significant step in the output signal. A slow RC time constant due to either a large resistive or capacitive load has a clipped corner on the output signal. The step is observed more prominently during a falling transition from high to low.

The plot in [Figure 29](#) shows the output for single 5-V supply with a 100-k Ω resistor. The step is at 1.3 V.

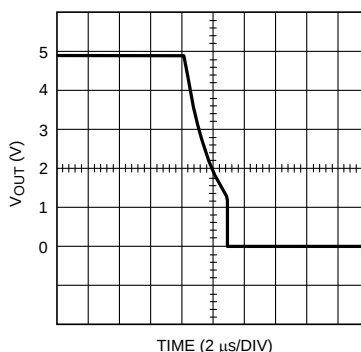


Figure 29. Output Signal Without Capacitive Load

The plot in [Figure 30](#) shows the output signal when a 20-pF capacitor is added as a load. The step is at about 2.5 V.

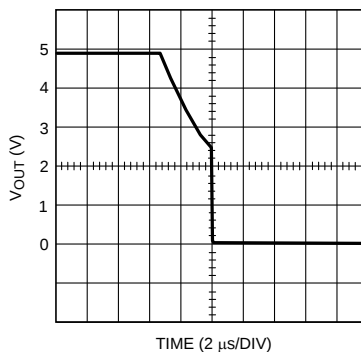


Figure 30. Output Signal With 20-pF Load

7.4 Device Functional Modes

7.4.1 Capacitive and Resistive Loads

The propagation delay is not affected by capacitive loads at the output of the LPV7215. However, resistive loads slightly affect the propagation delay on the falling edge by a reduction of almost 2 μs depending on the load resistance value.

7.4.2 Noise

Most comparators have rather low gain. This allows the output to spend time between high and low when the input signal changes slowly. The result is that the output may oscillate between high and low when the differential input is near zero. The exceptionally high gain of this comparator, 120 dB, eliminates this problem. Less than 1 μV of change on the input drives the output from one rail to the other rail. If the input signal is noisy, the output cannot ignore the noise unless some hysteresis is provided by positive feedback (see [Hysteresis](#)).

7.4.3 Hysteresis

To improve propagation delay when low overdrive is needed, hysteresis can be added.

7.4.4 Inverting Comparator With Hysteresis

The inverting comparator with hysteresis requires a three resistor network that is referenced to the supply voltage V^+ of the comparator as shown in [Figure 31](#). When V_{IN} at the inverting input is less than V_A , the voltage at the noninverting node of the comparator ($V_{\text{IN}} < V_A$), the output voltage is high (for simplicity assume V_O switches as high as V^+). The three network resistors can be represented as $R_1//R_3$ in series with R_2 .

The lower input trip voltage V_{A1} is defined as [Equation 1](#).

$$V_{A1} = V_{CC}R_2 / ((R_1//R_3) + R_2) \quad (1)$$

When V_{IN} is greater than V_A , the output voltage is low or very close to ground. In this case the three network resistors can be presented as $R_2//R_3$ in series with R_1 .

The upper trip voltage V_{A2} is defined as [Equation 2](#).

$$V_{A2} = V_{CC} (R_2//R_3) / ((R_1 + (R_2//R_3)) \quad (2)$$

The total hysteresis provided by the network is defined as $\Delta V_A = V_{A1} - V_{A2}$, as shown in [Equation 3](#).

$$\Delta V_A = \frac{+V_{CC}R_1R_2}{R_1R_2 + R_1R_3 + R_2R_3} \quad (3)$$

Device Functional Modes (continued)

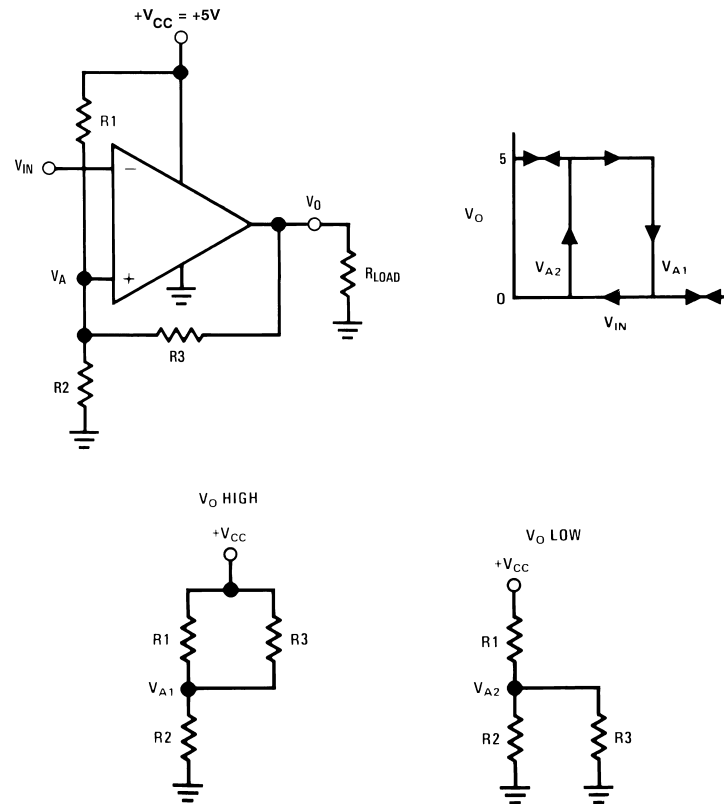


Figure 31. Inverting Comparator With Hysteresis

7.4.5 Noninverting Comparator With Hysteresis

A noninverting comparator with hysteresis requires a two resistor network, and a voltage reference (V_{REF}) at the inverting input. When V_{IN} is low, the output is also low. For the output to switch from low to high, V_{IN} must rise up to V_{IN1} where V_{IN1} is calculated by Equation 4.

$$V_{IN1} = \frac{V_{REF}(R_1 + R_2)}{R_2} \quad (4)$$

As soon as V_O switches to V_{CC} , V_A steps to a value greater than V_{REF} , which is given by Equation 5.

$$V_A = V_{IN} + \frac{(V_{CC} - V_{IN1})R_1}{R_1 + R_2} \quad (5)$$

To make the comparator switch back to its low state, V_{IN} must equal V_{REF} before V_A again equals V_{REF} . V_{IN2} can be calculated by Equation 6.

$$V_{IN2} = \frac{V_{REF}(R_1 + R_2) - V_{CC} R_1}{R_2} \quad (6)$$

The hysteresis of this circuit is the difference between V_{IN1} and V_{IN2} , as shown in Equation 7.

$$\Delta V_{IN} = V_{CC} R_1 / R_2 \quad (7)$$

Device Functional Modes (continued)

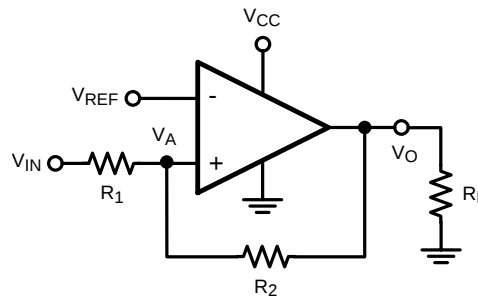


Figure 32. Noninverting Comparator With Hysteresis

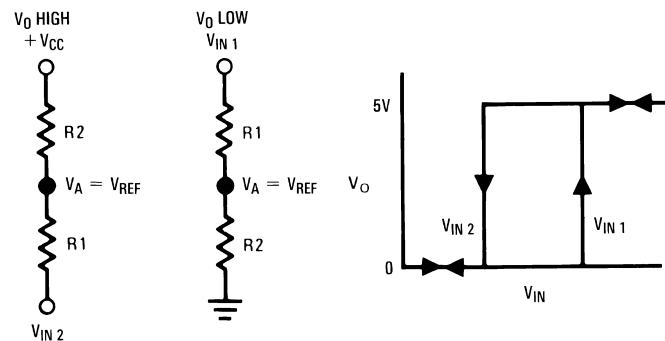


Figure 33. Noninverting Comparator With Hysteresis

7.4.6 Zero Crossing Detector

In a zero crossing detector circuit, the inverting input is connected to ground and the noninverting input is connected to a 100-mV_{PP} AC signal. As the signal at the noninverting input crosses 0 V, the comparator's output changes state.

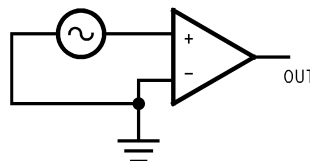


Figure 34. Zero Crossing Detector

To improve switching times and to center the input threshold to ground a small amount of positive feedback is added to the circuit. The voltage divider, R_4 and R_5 , establishes a reference voltage, V_1 , at the positive input. By making the series resistance, R_1 plus R_2 equal to R_5 , the switching condition, $V_1 = V_2$, is satisfied when $V_{IN} = 0$. The positive feedback resistor, R_6 , is made very large with respect to R_5 ($R_6 = 2000 R_5$). The resultant hysteresis established by this network is very small ($\Delta V_1 < 10 \text{ mV}$) but it is sufficient to insure rapid output voltage transitions. Diode D_1 is used to insure that the inverting input terminal of the comparator never goes below approximately -100 mV . As the input terminal goes negative, D_1 will forward bias, clamping the node between R_1 and R_2 to approximately -700 mV . This sets up a voltage divider with R_2 and R_3 preventing V_2 from going below ground. The maximum negative input overdrive is limited by the current handling ability of D_1 .

Device Functional Modes (continued)

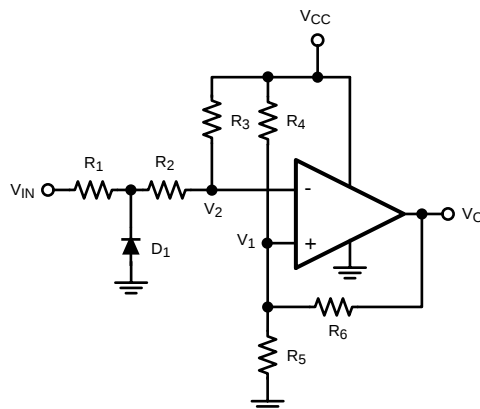


Figure 35. Zero Crossing Detector With Positive Feedback

7.4.7 Threshold Detector

Instead of tying the inverting input to 0 V, the inverting input can be tied to a reference voltage. As the input on the noninverting input passes the V_{REF} threshold, the comparator's output changes state. It is important to use a stable reference voltage to ensure a consistent switching point.

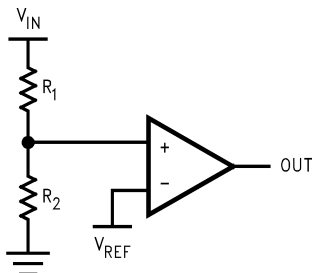


Figure 36. Threshold Detector

8 Application and Implementation

NOTE

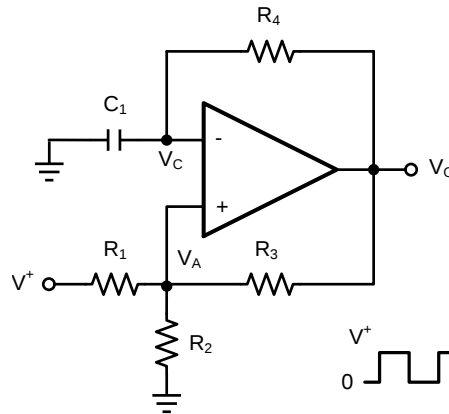
Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

8.1 Application Information

The LPV7215 is an ultra-low-power comparator with a typical power supply current of 580 nA. It has the best-in-class power supply current versus propagation delay performance available among TI's low-power comparators. The propagation delay is as low as 4.5 μ s with 100-mV overdrive at 1.8-V supply.

8.2 Typical Applications

8.2.1 Square Wave Generator



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Figure 37. Square Wave Generator Schematic

8.2.1.1 Design Requirements

A typical application for a comparator is as a square wave oscillator. The circuit in [Figure 38](#) generates a square wave whose period is set by the RC time constant of the capacitor C_1 and resistor R_4 . The maximum frequency is limited by the large signal propagation delay of the comparator and by the capacitive loading at the output, which limits the output slew rate.

8.2.1.2 Detailed Design Procedure

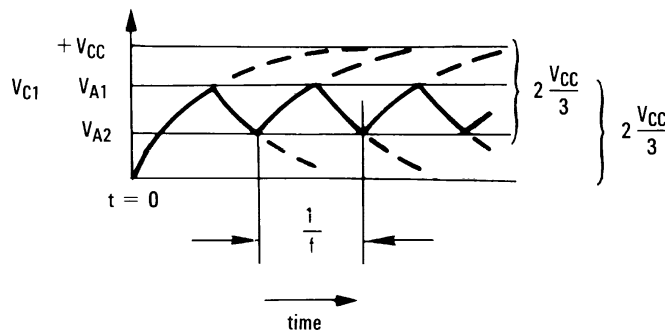


Figure 38. Square Wave Oscillator

Typical Applications (continued)

Consider the output of [Figure 38](#) to be high to analyze the circuit. That implies that the inverted input (V_C) is lower than the noninverting input (V_A). This causes the C_1 to be charged through R_4 , and the voltage V_C increases until it is equal to the noninverting input. The value of V_A at this point is in [Equation 8](#).

$$V_{A1} = \frac{V_{CC} \times R_2}{R_2 + R_1 \parallel R_3} \quad (8)$$

If $R_1 = R_2 = R_3$ then $V_{A1} = 2 V_{CC}/3$

At this point the comparator switches pulling down the output to the negative rail. The value of V_A at this point, as shown in [Equation 9](#):

$$V_{A2} = \frac{V_{CC}(R_2 \parallel R_3)}{R_1 + (R_2 \parallel R_3)} \quad (9)$$

If $R_1 = R_2 = R_3$ then $V_{A2} = V_{CC}/3$

The capacitor C_1 now discharges through R_4 , and the voltage V_C decreases until it is equal to V_{A2} , at which point the comparator switches again, bringing it back to the initial stage. The time period is equal to twice the time it takes to discharge C_1 from $2 V_{CC}/3$ to $V_{CC}/3$, which is given by $R_4 C_1 \times \ln 2$. Hence the formula for the frequency is given by [Equation 10](#):

$$F = 1/(2 \times R_4 \times C_1 \times \ln 2) \quad (10)$$

8.2.1.3 Application Curves

[Figure 39](#) shows the simulated results of an oscillator using the following values:

1. $R_1 = R_2 = R_3 = R_4 = 100 \text{ k}\Omega$
2. $C_1 = 100 \text{ pF}$, $C_L = 20 \text{ pF}$
3. $V_+ = 5 \text{ V}$, $V_- = \text{GND}$
4. C_{STRAY} (not shown) from V_a to $\text{GND} = 10 \text{ pF}$

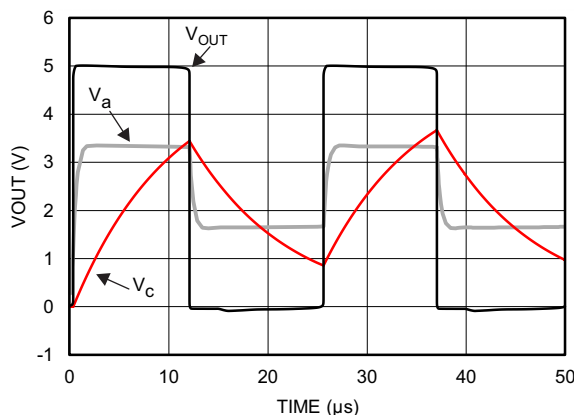


Figure 39. Square Wave Oscillator Output Waveform

Typical Applications (continued)

8.2.2 Window Detector

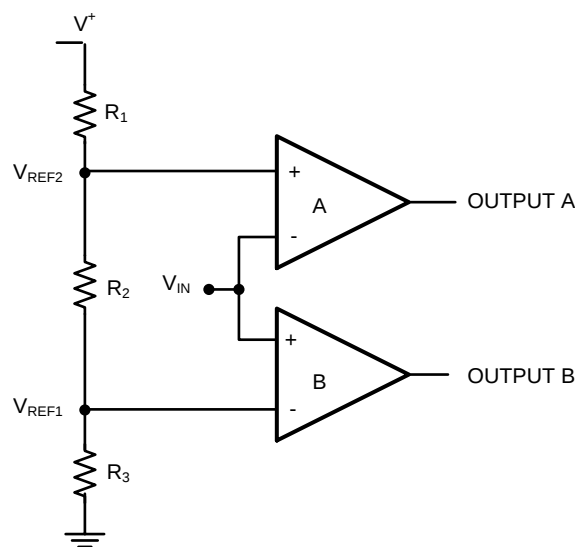
A window detector monitors the input signal to determine if it falls between two voltage levels.

The comparator outputs A and B are high only when $V_{REF1} < V_{IN} < V_{REF2}$ or *within the window*. These are defined as:

$$V_{REF1} = R_3 / (R_1 + R_2 + R_3) \times V^+ \quad (11)$$

$$V_{REF2} = (R_2 + R_3) / (R_1 + R_2 + R_3) \times V^+ \quad (12)$$

Others names for window detectors are: threshold detector, level detectors, and amplitude trigger or detector.



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Figure 40. Window Detector

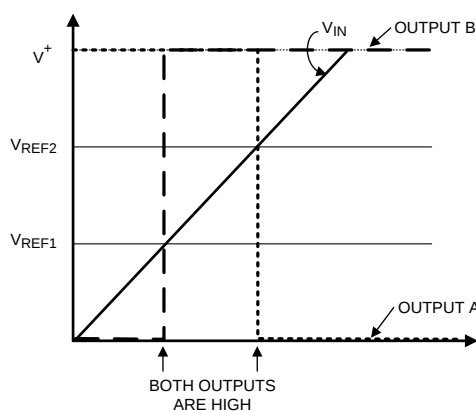
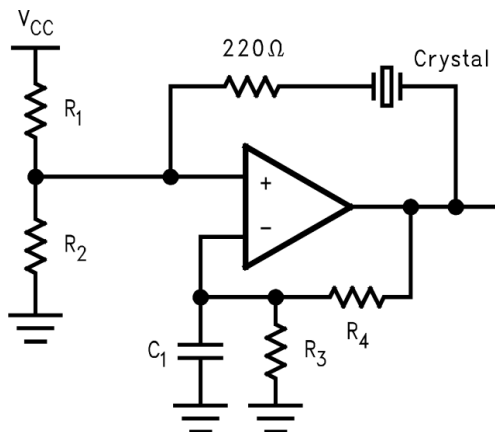


Figure 41. Window Detector Output Signal

Typical Applications (continued)

8.2.3 Crystal Oscillator

A simple crystal oscillator using the LPV7215 is shown in [Figure 42](#). Resistors R_1 and R_2 set the bias point at the comparator's noninverting input. Resistors, R_3 and R_4 and capacitor C_1 set the inverting input node at an appropriate DC average level based on the output. The crystal's path provides resonant positive feedback and stable oscillation occurs. The output duty cycle for this circuit is roughly 50%, but it is affected by resistor tolerances and to a lesser extent by the comparator offset.

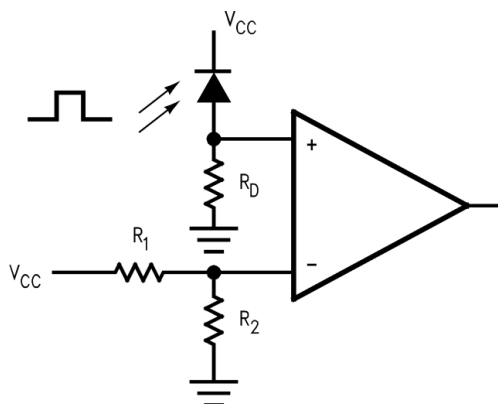


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Figure 42. Crystal Oscillator

8.2.4 IR Receiver

The LPV7215 can also be used as an infrared receiver. The infrared photo diode creates a current relative to the amount of infrared light present. The current creates a voltage across R_D . When this voltage level crosses the voltage applied by the voltage divider to the inverting input, the output transitions.



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Figure 43. IR Receiver

9 Power Supply Recommendations

Comparators are very sensitive to input noise. To minimize supply noise, power supplies must be capacitively decoupled by a 0.01- μ F ceramic capacitor in parallel with a 10- μ F electrolytic capacitor.

10 Layout

10.1 Layout Guidelines

Proper grounding and the use of a ground plane help ensure the specified performance of the LPV7215. Minimizing trace lengths, reducing unwanted parasitic capacitance and using surface-mount components also helps.

10.2 Layout Example

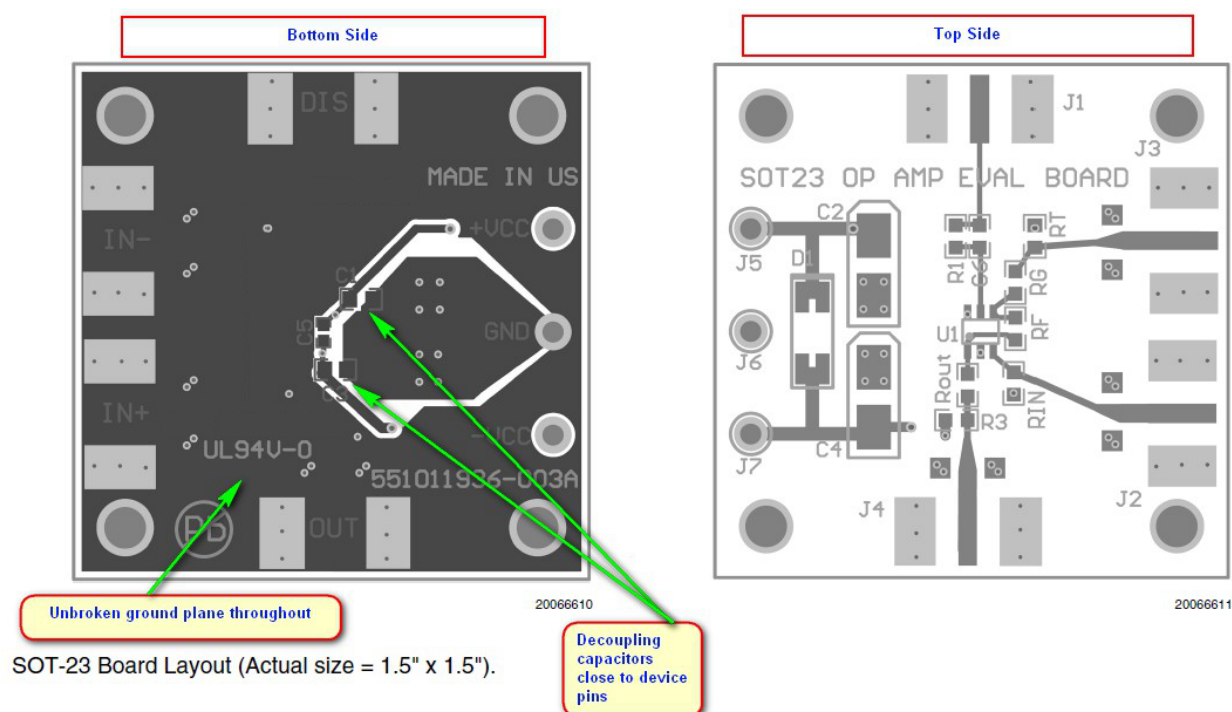


Figure 44. LPV7215 Layout Example

11 デバイスおよびドキュメントのサポート

11.1 デバイス・サポート

11.1.1 開発サポート

TINA-TI SPICEベース・アナログ・シミュレータ・プログラム、<http://www.ti.com/tool/tina-ti>

DIPアダプタ評価モジュール、<http://www.ti.com/tool/dip-adapter-evm>

TIユニバーサル・オペアンプ評価モジュール、<http://www.ti.com/tool/opampevm>

11.1.2 ドキュメントのサポート

11.1.2.1 関連資料

関連資料については、以下を参照してください。

『AN-74 - 独立に動作する4つのコンパレータ』(SNOA654)

11.2 ドキュメントの更新通知を受け取る方法

ドキュメントの更新についての通知を受け取るには、ti.comのデバイス製品フォルダを開いてください。右上の隅にある「通知を受け取る」をクリックして登録すると、変更されたすべての製品情報に関するダイジェストを毎週受け取れます。変更の詳細については、修正されたドキュメントに含まれている改訂履歴をご覧ください。

11.3 コミュニティ・リソース

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

TI E2E™ Online Community *TI's Engineer-to-Engineer (E2E) Community*. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

11.4 商標

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11.5 静電気放電に関する注意事項



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11.6 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

12 メカニカル、パッケージ、および注文情報

以降のページには、メカニカル、パッケージ、および注文に関する情報が記載されています。これらの情報は、指定のデバイスに対して提供されている最新のデータです。このデータは予告なく変更されることがあり、ドキュメントが改訂される場合もあります。本データシートのブラウザ版を使用されている場合は、画面左側の説明をご覧ください。

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
LPV7215MF/NOPB	Active	Production	SOT-23 (DBV) 5	1000 SMALL T&R	Yes	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	C30A
LPV7215MF/NOPB.A	Active	Production	SOT-23 (DBV) 5	1000 SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C30A
LPV7215MFX/NOPB	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	C30A
LPV7215MFX/NOPB.A	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C30A
LPV7215MG/NOPB	Active	Production	SC70 (DCK) 5	1000 SMALL T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	C37
LPV7215MG/NOPB.A	Active	Production	SC70 (DCK) 5	1000 SMALL T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	C37
LPV7215MGX/NOPB	Active	Production	SC70 (DCK) 5	3000 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	C37
LPV7215MGX/NOPB.A	Active	Production	SC70 (DCK) 5	3000 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	C37

⁽¹⁾ **Status:** For more details on status, see our [product life cycle](#).

⁽²⁾ **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

⁽⁴⁾ **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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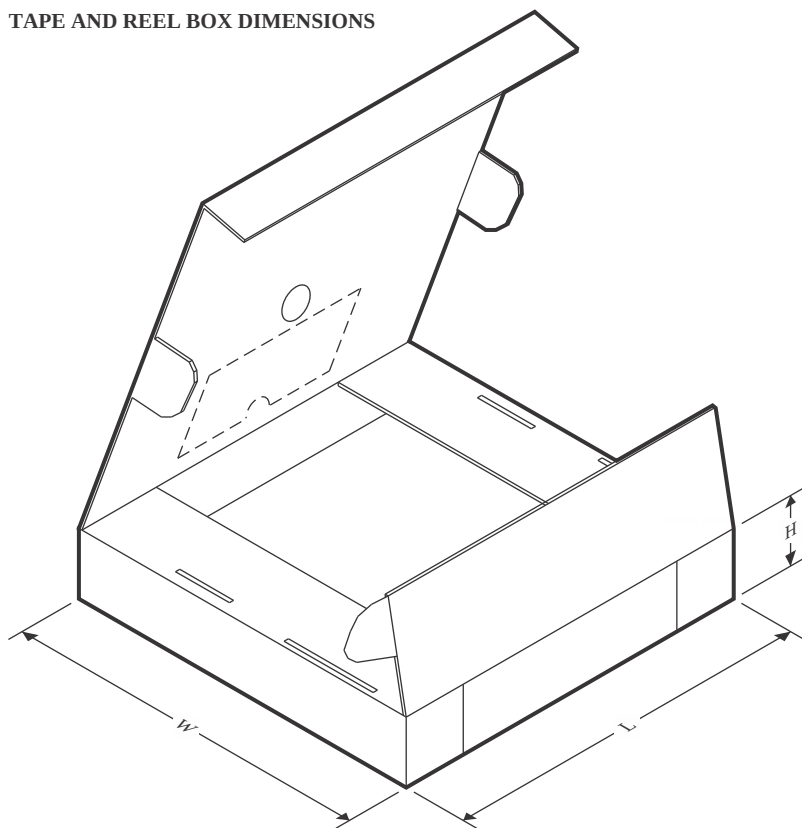
TAPE AND REEL INFORMATION



*All dimensions are nominal

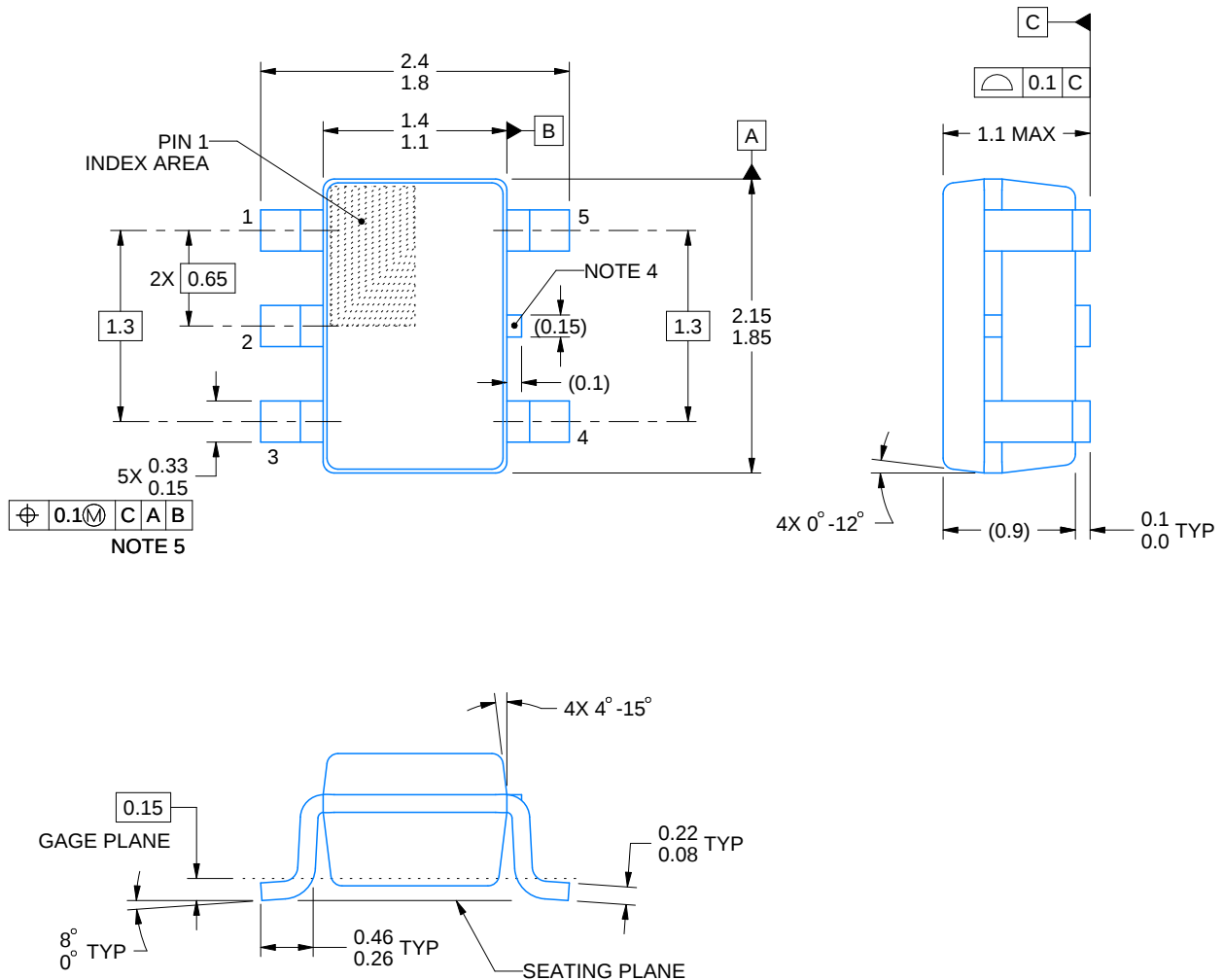
Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
LPV7215MF/NOPB	SOT-23	DBV	5	1000	178.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
LPV7215MF/NOPB	SOT-23	DBV	5	1000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
LPV7215MFX/NOPB	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
LPV7215MFX/NOPB	SOT-23	DBV	5	3000	178.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
LPV7215MG/NOPB	SC70	DCK	5	1000	178.0	8.4	2.25	2.45	1.2	4.0	8.0	Q3
LPV7215MGX/NOPB	SC70	DCK	5	3000	178.0	8.4	2.25	2.45	1.2	4.0	8.0	Q3

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
LPV7215MF/NOPB	SOT-23	DBV	5	1000	208.0	191.0	35.0
LPV7215MF/NOPB	SOT-23	DBV	5	1000	210.0	185.0	35.0
LPV7215MFX/NOPB	SOT-23	DBV	5	3000	210.0	185.0	35.0
LPV7215MFX/NOPB	SOT-23	DBV	5	3000	208.0	191.0	35.0
LPV7215MG/NOPB	SC70	DCK	5	1000	208.0	191.0	35.0
LPV7215MGX/NOPB	SC70	DCK	5	3000	208.0	191.0	35.0



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NOTES:

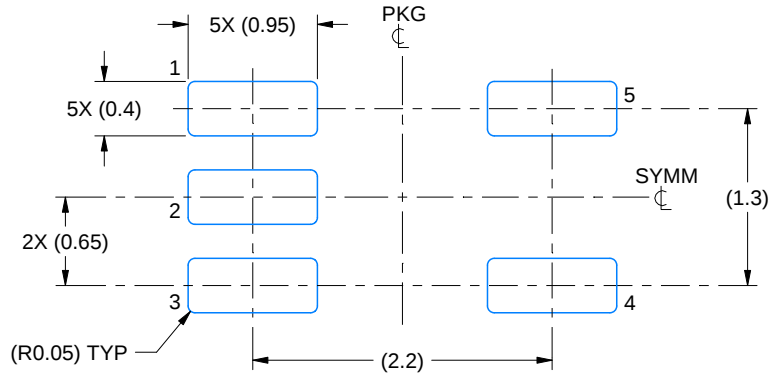
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Reference JEDEC MO-203.
4. Support pin may differ or may not be present.
5. Lead width does not comply with JEDEC.
6. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25mm per side

EXAMPLE BOARD LAYOUT

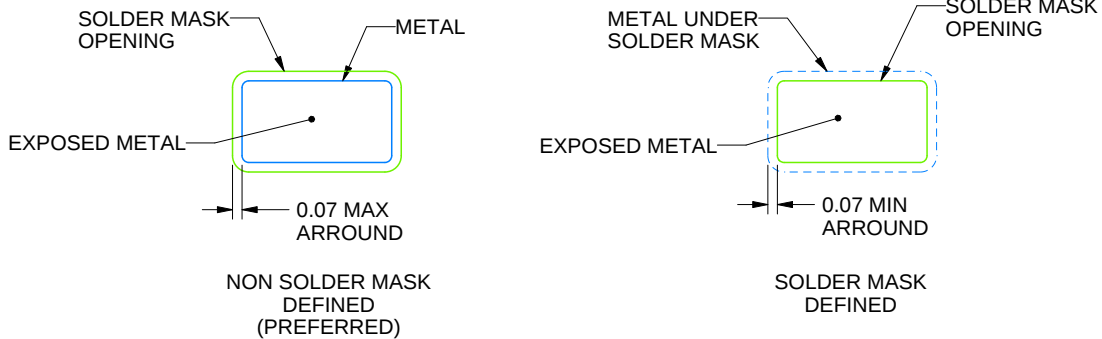
DCK0005A

SOT - 1.1 max height

SMALL OUTLINE TRANSISTOR



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:18X

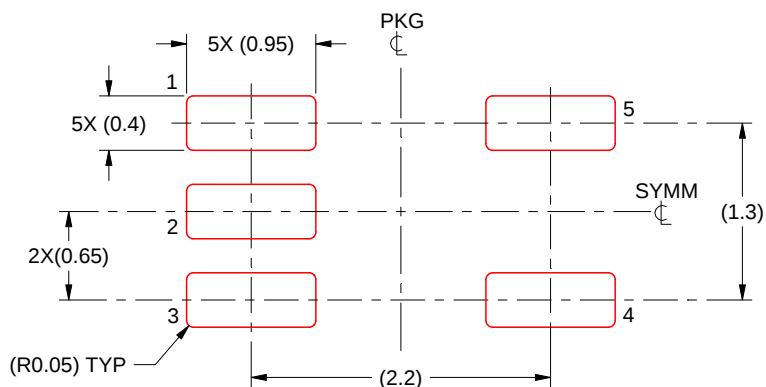


SOLDER MASK DETAILS

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NOTES: (continued)

7. Publication IPC-7351 may have alternate designs.
8. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.125 THICK STENCIL
SCALE:18X

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NOTES: (continued)

9. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
10. Board assembly site may have different recommendations for stencil design.



SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



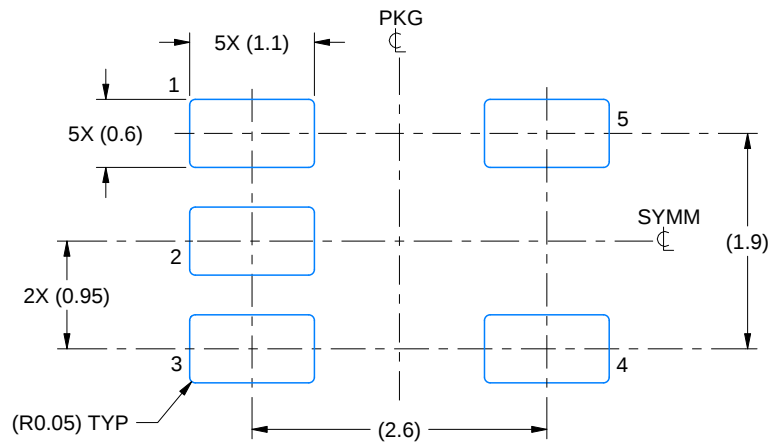
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Reference JEDEC MO-178.
4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25 mm per side.
5. Support pin may differ or may not be present.

EXAMPLE BOARD LAYOUT

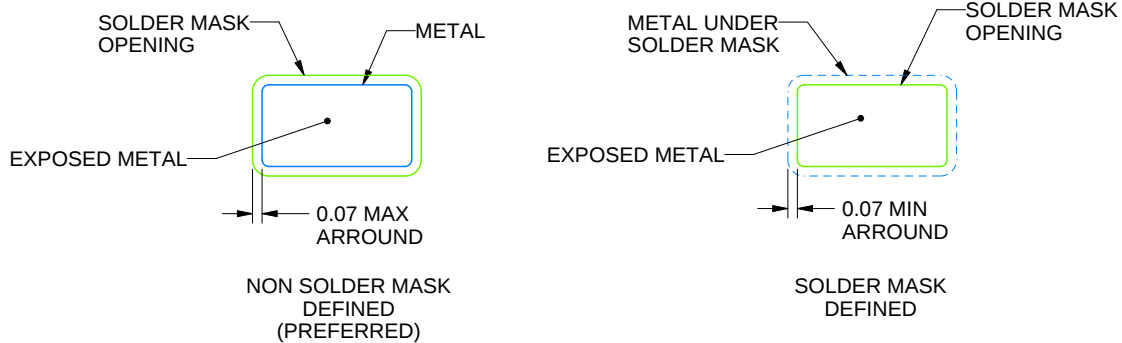
DBV0005A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:15X



SOLDER MASK DETAILS

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NOTES: (continued)

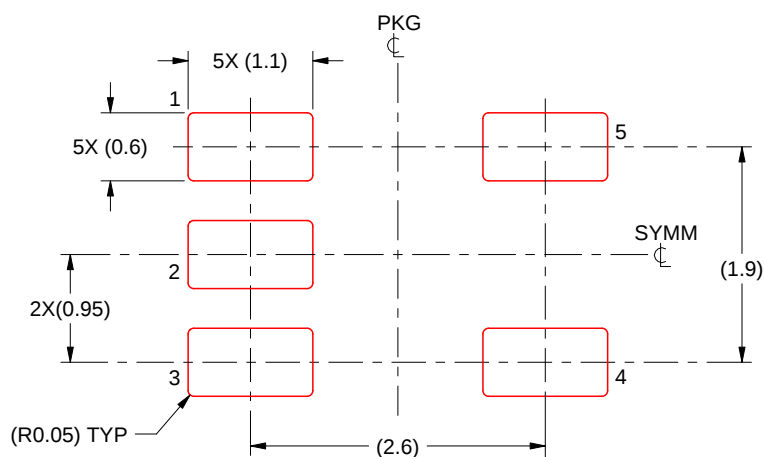
6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DBV0005A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:15X

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NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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